

Dual N-channel 60 V, 55 mΩ logic level MOSFET

24 February 2015

Product data sheet

### 1. General description

Dual logic level N-channel MOSFET in an LFPAK56D (Dual Power-SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

### 2. Features and benefits

- Dual MOSFET
- Q101 Compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with  $V_{GS(th)}$  rating of greater than 0.5 V at 175 °C

### 3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

### 4. Quick reference data

Table 1. Quie	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	60	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	16	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	32	W
Static characte	eristics FET1 and FET2						
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 12</u>		-	47.3	55	mΩ
Dynamic characteristics FET1 and FET2							
Q <sub>GD</sub>	gate-drain charge	$I_D = 5 \text{ A}; V_{DS} = 48 \text{ V}; V_{GS} = 5 \text{ V};$ $T_j = 25 \text{ °C}; \text{ Fig. 14}; \text{ Fig. 15}$		-	2.3	-	nC

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# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1		D1 D1 D2 D2
2	G1	gate1		
3	S2	source2		
4	G2	gate2		
5	D2	drain2		 S1 G1 S2 G2
6	D2	drain2		mbk725
7	D1	drain1	1 2 3 4 LFPAK56D (SOT1205)	
8	D1	drain1		

# 6. Ordering information

Table 3.Ordering in	formation					
Type number	Package					
	Name	Description	Version			
BUK9K52-60E	LFPAK56D	Plastic single ended surface mounted package (LFPAK56D); 8 leads	SOT1205			

### 7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK9K52-60E	95260E

# 8. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	60	V
V <sub>DGR</sub>	drain-gate voltage	R <sub>GS</sub> = 20 kΩ; T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	60	V
V <sub>GS</sub>	gate-source voltage	T <sub>j</sub> ≤ 175 °C; DC		-10	10	V
		$T_j \le 175 \ ^{\circ}C; Pulsed$	[1][2]	-15	15	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	32	W
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 5 V; <u>Fig. 2</u>		-	16	А
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 5 V; <u>Fig. 2</u>		-	11	А
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# **BUK9K52-60E**

#### Dual N-channel 60 V, 55 mΩ logic level MOSFET

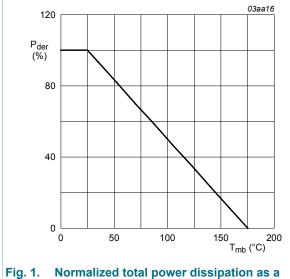
Symbol	Parameter	Conditions		Min	Max	Unit
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 3	3	-	64	А
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-drai	n diode FET1 and FET2					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	16	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$		-	64	А
Avalanche r	uggedness FET1 and FET2					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D = 16 \text{ A}; V_{sup} \le 60 \text{ V}; V_{GS} = 5 \text{ V};$ $T_{j(init)} = 25 \text{ °C}; Fig. 4$	[3][4]	-	11.9	mJ

Accumulated Pulse duration up to 50 hours delivers zero defect ppm [1]

[2] Significantly longer life times are achieved by lowering  $\rm T_{i}$  and or  $\rm V_{GS}$ 

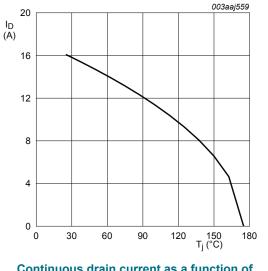
[3] [4] Refer to application note AN10273 for further information

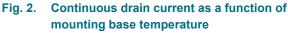
Single-pulse avalanche rating limited by maximum junction temperature of 175 °C



function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

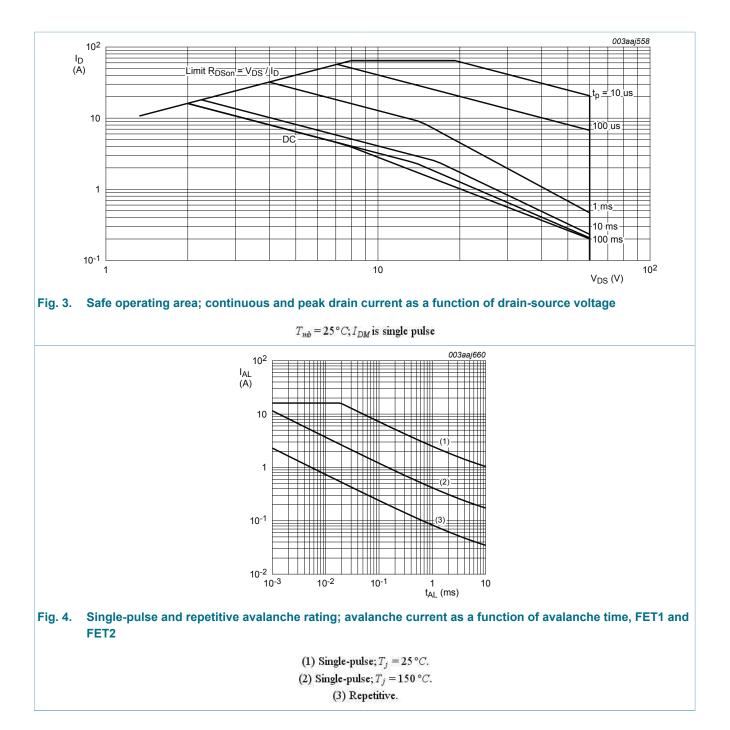




 $V_{GS} \ge 5V$ 

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### 9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	4.68	K/W

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Symbol	Parameter	Conditions			Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	Minimum foot printed circuit	print; mounted on a board		-	95	-	K/W
(K/W)	δ = 0.5						03aaj557	
10 <sup>-1</sup>	0.02 0.02 single shot				P		$=\frac{t_p}{T}$	
10 <sup>-2</sup> 10 <sup>-6</sup>	10 <sup>-5</sup>	10 <sup>-4</sup>	10 <sup>-3</sup>	10 <sup>-2</sup>	10 <sup>-1</sup>	t <sub>p</sub> (s)	1	
ig. 5. Tra	nsient thermal impedanc	e from junction	to mounting base	as a function	of pulse	duratio	on	

### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics FET1 and FET2	· · · · · · · · · · · · · · · · · · ·	I		1	
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	54	-	-	V
	breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	60	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 10; Fig. 11	1.4	1.7	2.1	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; Fig. 10; Fig. 11	0.5	-	-	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; Fig. 10; Fig. 11	-	-	2.45	V
I <sub>DSS</sub> drain leakage current	drain leakage current	$V_{DS}$ = 60 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.02	1	μA
		V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = -10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
		$V_{GS}$ = 10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 12</u>	-	47.3	55	mΩ
	resistance	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 175 °C; Fig. 12; Fig. 13	-	106.9	124.3	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 12</u>	-	41.4	49	mΩ

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic cl	haracteristics FET1 and FE	ET2	II			
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 5 A; V <sub>DS</sub> = 48 V; V <sub>GS</sub> = 5 V;	-	5.6	-	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C; <u>Fig. 14</u> ; <u>Fig. 15</u>	-	1.1	-	nC
Q <sub>GD</sub>	gate-drain charge	-	-	2.3	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS}$ = 0 V; $V_{DS}$ = 25 V; f = 1 MHz;	-	544	725	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 16</u>	-	74	89	pF
C <sub>rss</sub>	reverse transfer capacitance		-	40	55	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 48 V; R <sub>L</sub> = 10 Ω; V <sub>GS</sub> = 5 V;	-	6.2	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C; I_D = 5 A$	-	10.1	-	ns
t <sub>d(off)</sub>	turn-off delay time	-	-	10.7	-	ns
t <sub>f</sub>	fall time	-	-	9	-	ns
Source-dra	in diode FET1 and FET2		II			
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 5 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <u>Fig. 17</u>	-	0.78	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S} = 5 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$	-	17.7	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 30 V; T <sub>j</sub> = 25 °C	-	11.6	-	nC

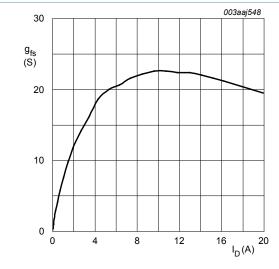
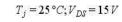
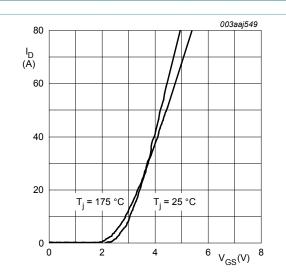


Fig. 6. Forward transconductance as a function of drain current; typical values

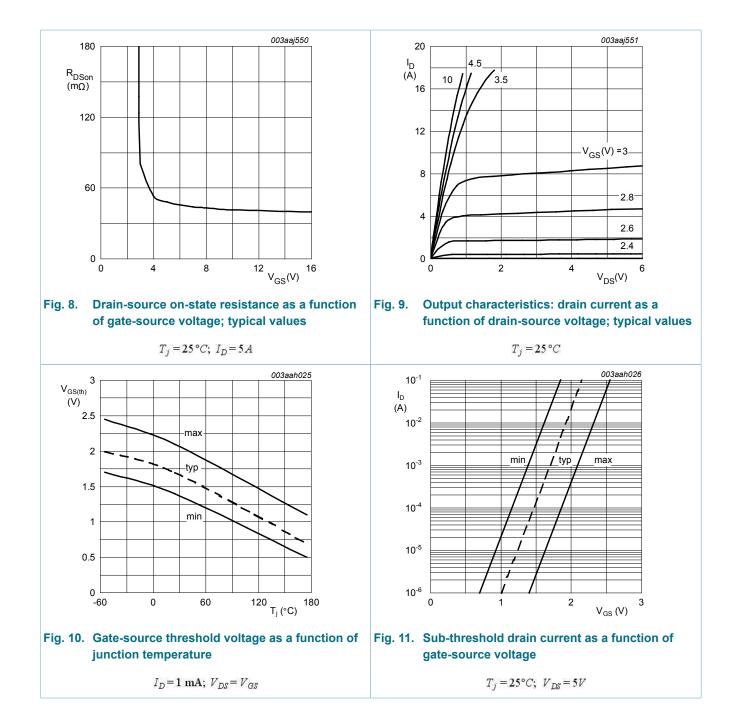




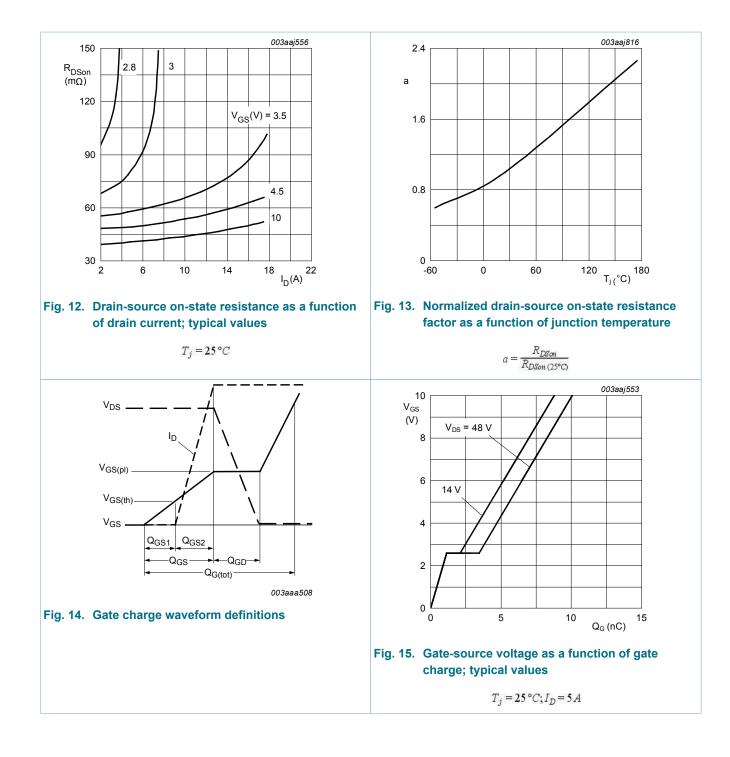


 $V_{DS} = 10V$ 

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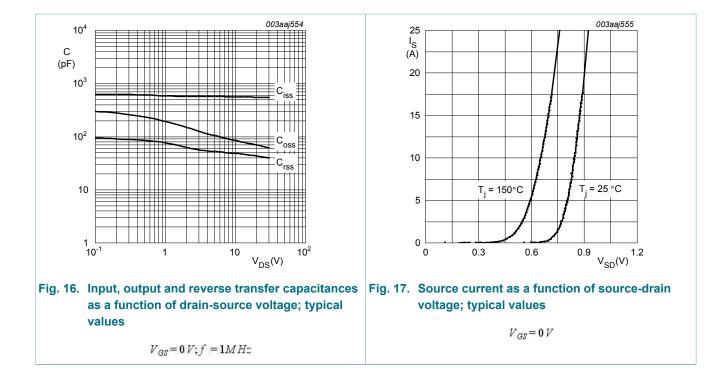
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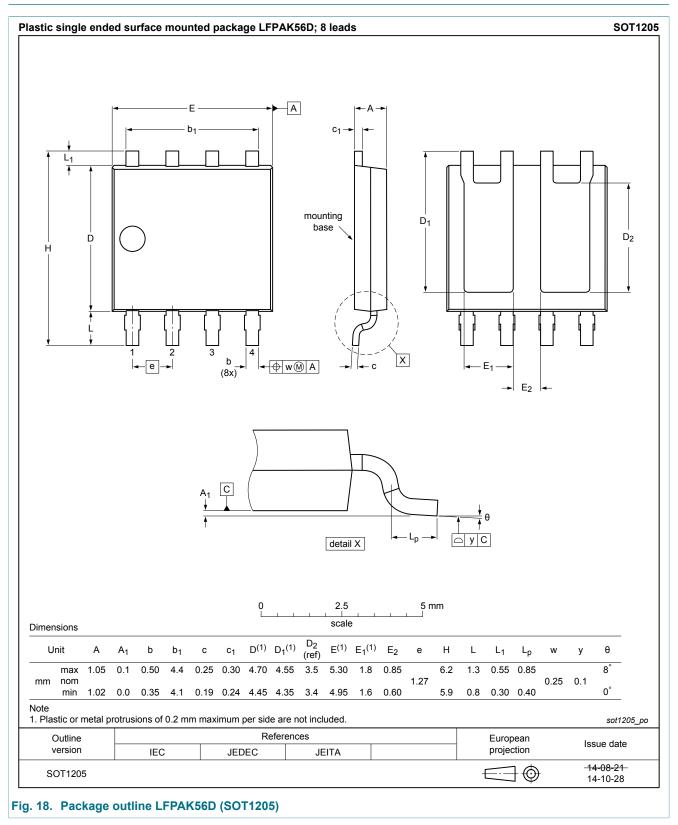
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### **11. Package outline**



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Product data sheet

#### Dual N-channel 60 V, 55 mΩ logic level MOSFET

### 12. Legal information

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Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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